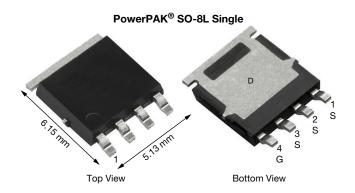


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Vishay Siliconix

Automotive P-Channel 200 V (D-S) 175 °C MOSFET



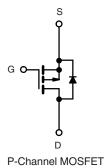
PRODUCT SUMMARY				
V _{DS} (V)	-200			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.305			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -6 \text{ V}$	0.315			
I _D (A)	-9.4			
Configuration	Single			

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912







ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ431AEP (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unles	ss otherwise noted)			
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	-200	V	
Gate-source voltage		V_{GS}	± 20		
Continuous drain current	T _C = 25 °C	I-	-9.4		
Continuous drain current	T _C = 125 °C	I _D	-5.4		
Continuous source current (diode conduction)		Is	-60	Α	
Pulsed drain current ^a		I _{DM}	-37		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-30		
Single pulse avalanche energy	L = 0.1 IIII1	E _{AS}	45	mJ	
Maximum power dissipation ^a	T _C = 25 °C	D	68	W	
Maximum power dissipation =	$T_{\rm C} = 125 ^{\circ}{\rm C}$	P_{D}	22	VV	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature	re) ^{c, d}		260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction to ambient PC	CB mount b	R_{thJA}	68	°C/W
Junction to case (drain)		R_{thJC}	2.2	C/VV

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)

S22-0060-Rev. B, 24-Jan-2022

- c. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = -250 μA	-200	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = -250 μA	-2.5	-3.0	-3.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -200 V	-	-	-1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -200 V, T _J = 125 °C	-	-	-50	μΑ
		V _{GS} = 0 V	V _{DS} = -200 V, T _J = 175 °C	-	-	-150	
On-state drain current a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 \text{ V}$	-5	-	-	Α
		V _{GS} = -10 V	I _D = -3.8 A	-	0.254	0.305	
Duta a superior del control de co		V _{GS} = -10 V	I _D = -3.8 A, T _J = 125 °C	-	-	0.591	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = -10 V	I _D = -3.8 A, T _J = 175 °C	-	-	0.763	Ω
		V _{GS} = -6 V	I _D = -3.8 A	-	0.261	0.315	
Forward transconductance b	9fs	V _{DS} =	-15 V, I _D = -3.8 A	-	15	-	S
Dynamic ^b							
Input capacitance	C _{iss}			-	2734	3700	
Output capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = -25 V, f = 1 MHz	-	155	210	рF
Reverse transfer capacitance	C _{rss}			-	103	140	
Total gate charge ^c	Qg			-	55	85	
Gate-source charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -100 \text{ V}, I_{D} = -5.2 \text{ A}$	-	11	-	nC
Gate-drain charge ^c	Q_{gd}			-	17	-	
Gate resistance	R _g		f = 1 MHz	0.6	1.25	1.9	Ω
Turn-on delay time ^c	t _{d(on)}			-	16	25	
Rise time ^c	t _r	V _{DD} = -	-100 V, $R_L = 20.8 \Omega$	-	5	10	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong -4.8 A$	V_{GEN} = -10 V, R_g = 1 Ω	-	35	55	ns
Fall time ^c	t _f			-	5	10	
Source-Drain Diode Ratings and Chara	acteristics b						
Pulsed current ^a	I _{SM}			-	-	-37	Α
Forward voltage	V _{SD}	IF	I _F = -5 A, V _{GS} = 0		-0.8	-1.2	V
Body diode reverse recovery time	t _{rr}			-	101	205	ns
Body diode reverse recovery charge	Q _{rr}] , ,	A di/dt = 100 A/::-	-	52	105	nC
Reverse recovery fall time	ta	$ I_F = -4 $	A, di/dt = 100 A/μs	-	87	-	na
Reverse recovery rise time	t _b	7		-	14	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	-11.3	-	Α

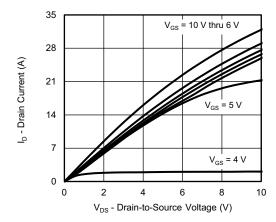
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

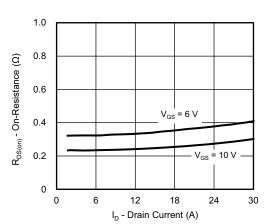
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



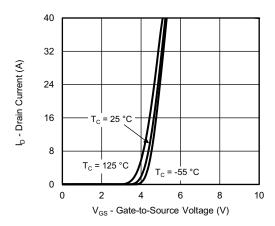
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



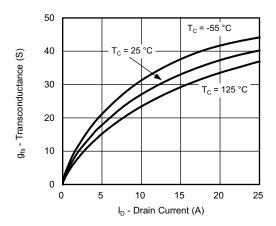
Output Characteristics



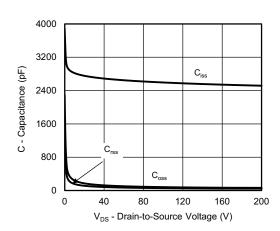
On-Resistance vs. Drain Current



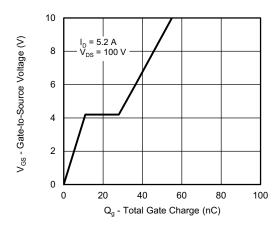
Transfer Characteristics



Transconductance



Capacitance

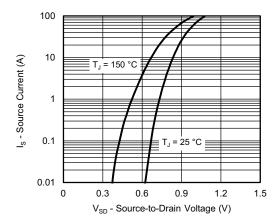


Gate Charge

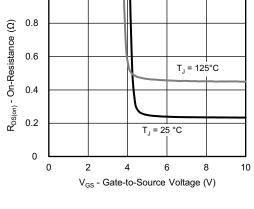
For technical questions, contact: automostechsupport@vis



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

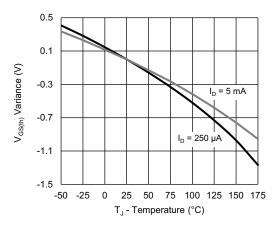


Source Drain Diode Forward Voltage

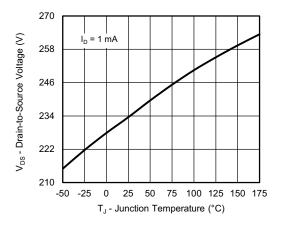


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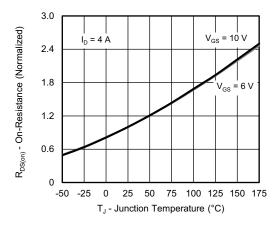
On-Resistance vs. Gate-to-Source Voltage



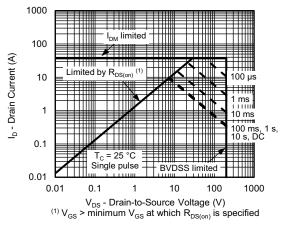
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



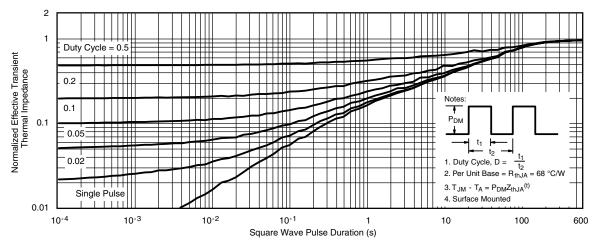
On-Resistance vs. Junction Temperature



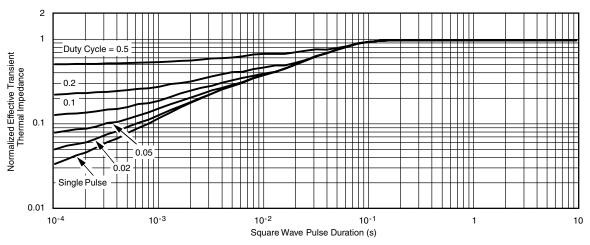
Safe Operating Area



THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

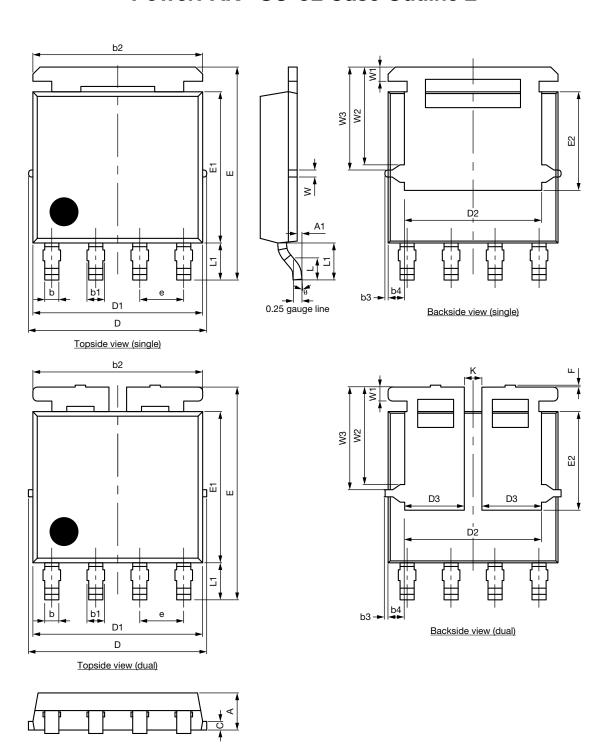
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part

pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg275999.



PowerPAK® SO-8L Case Outline 2



Revision: 01-Nov-2021 1 Document Number: 66934



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DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	X. MIN. NOM. N		MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51	•	0.020			
W	0.23			0.009			
W1	0.41		0.016				
W2	2.82		0.111				
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

ECN: C21-1498-Rev. C, 01-Nov-2021

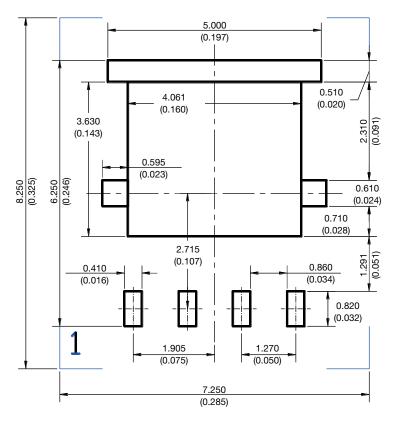
DWG: 6044

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

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